



FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

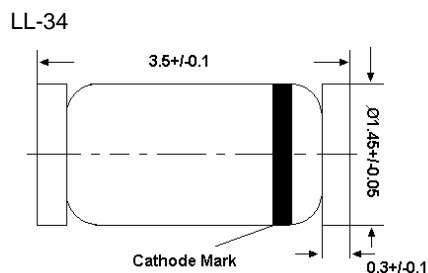
TEL: 852-2790 0314 FAX: 852-2790 0206

LL4150

SILICON EPITAXIAL PLANAR DIODE

Features

- Fast Switching Speed
- High Reliability
- High Conductance
- For General Purpose Switching Applications



Glass case MiniMELF
Dimensions in mm

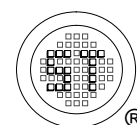
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	50	V
Forward Continuous Current	I_{FM}	300 ¹⁾	mA
Average Rectified Output Current	I_O	200 ¹⁾	mA
Power Dissipation Derate Above 25°C	P_{tot}	500 ¹⁾ 1.68	mW mW/°C
Junction temperature	T_J	200	°C
Operating and Storage Temperature Range	T_S	-65 to +175	°C

¹⁾ Valid provided that leads are at a distance of 8 mm from case kept at ambient temperature

Characteristics at $T_J = 25^\circ\text{C}$

	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 200\text{mA}$	V_F	-	1.2	V
Peak Reverse Current at $V_R = 50\text{V}$	I_R	-	100	nA
Reverse Recovery Time at $I_F = I_R = 10$ to 200mA , to $0.1 I_F$	T_{rr}	-	4	nS



Dated : 05/10/2005